

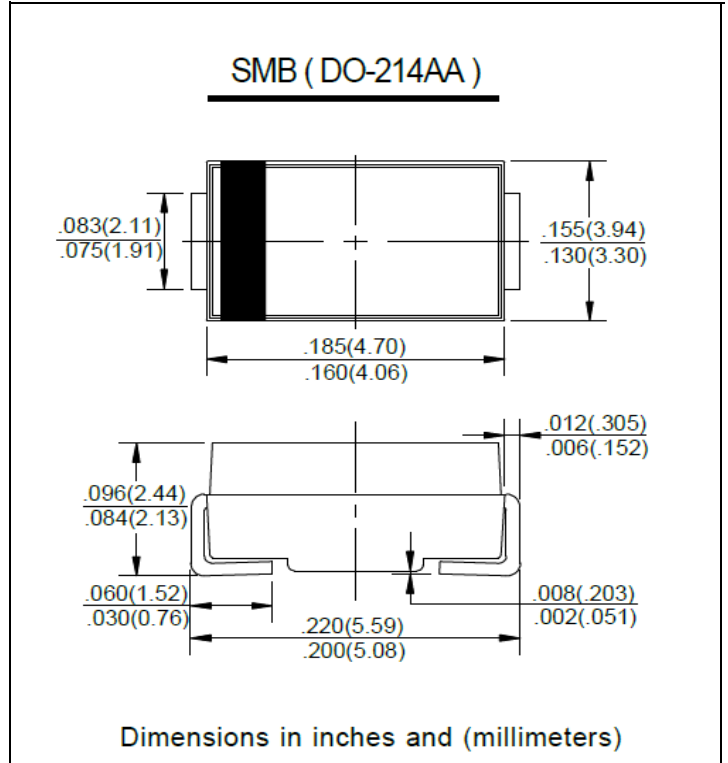


FEATURES

- For surface mounted applications
- Metal-Semiconductor junction with guardring
- Epitaxial construction
- Low forward voltage drop
- High current capability
- For sue in low voltage,high frequency inverters free wheeling,and polarity protection applications
- The plastic material carries U/L recognition 94V-O

MECHANICAL DATA

- Case: JEDEC DO - 214Ab. molded plastic
- Polarity: Color band denotes cathode
- Weight: 0.009 ounce.0.25 grams



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

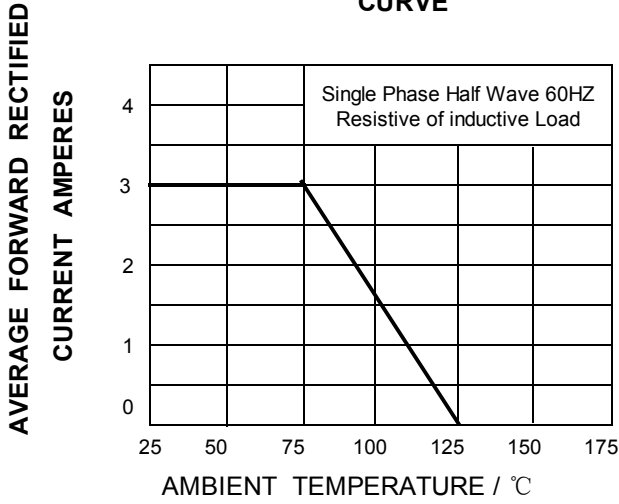
Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase. half wave. 60HZ. resistive or inductive load. For capacitive load. derate current by 20%

	SYMBOL	SS32	SS33	SS34	SS35	SS36	UNITS
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	20	30	40	50	60	V
Maximum RMS Voltage	V _{RMS}	14	21	28	35	42	V
Maximum DC Blocking Voltage	V _{DC}	20	30	40	50	60	V
Maximum Average Forward Rectified Current at T _L = 100°C	I _(AV)	3.0					A
Peak Forward Surge Current 8.3ms Single half-sine-wave superimposed on rated load	I _{FSM}	100					A
Maximum Forward Voltage at 3.0A DC	V _F	0.5			0.7		V
Maximum Reverse Current T _j = 25°C at Rated DC Blocking Voltage T _j = 100°C	I _R	0.5					mA
Typical Junction Capacitance (Note 1)	C _j	250					pF
Typical Thermal Resistance (Note 2,	R _{QJL}	10					°C/W
	R _{QJA}	50					
Operating Junction Temperature Range	T _j	-55 to 125					°C
Storage Temperature Range	T _{STG}	-55 to 150					°C

- NOTE:
1. Measured at 1.0MHZ and applied reverse voltage of 4.0V DC.
 2. Thermal Resistance Junction to Lead.
 3. Thermal Resistance Junction to Ambient.

FIG. 1 -- FORWARD CURRENT DERATING CURVE



2 -- MAXIMUM NON-REPETITIVE SURGE

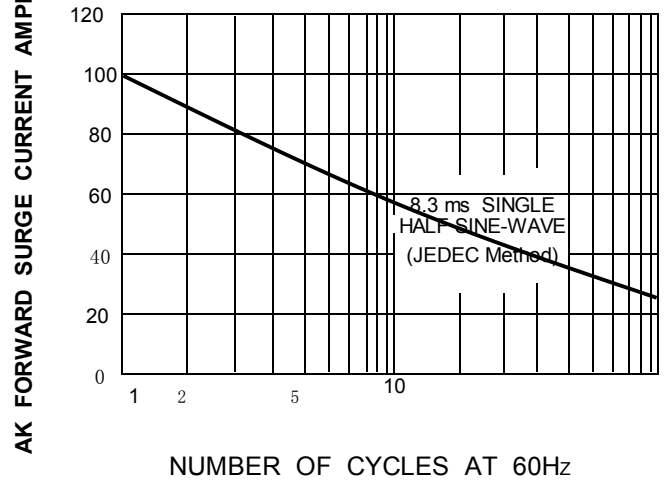
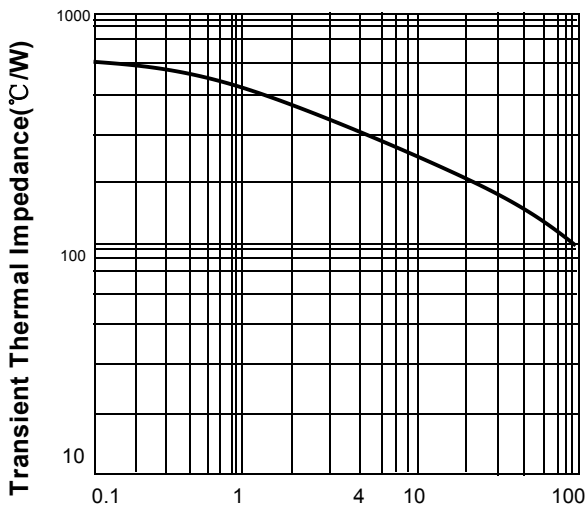


Fig.3-TYPICAL JUNCTION CAPACITANCE



g.4-TYPICAL FORWARD CHARACTERISTIC

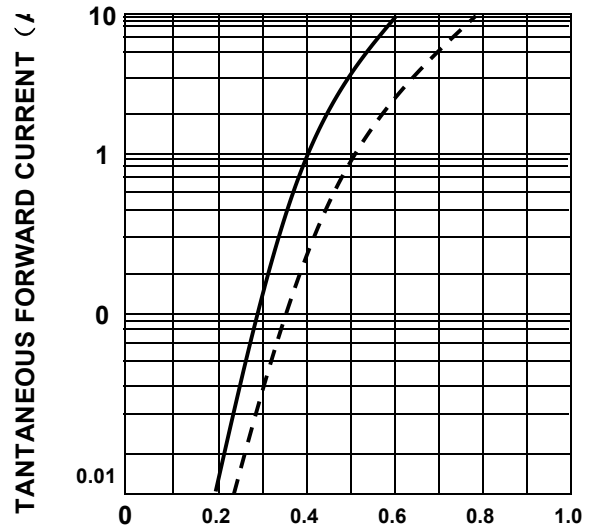


Fig.5-TYPICAL REVERSE CHARACTERISTICS

